



## STP9NK60Z Information



For Reference Only

Part Number STP9NK60Z

Manufacturer STMicroelectronics

**Category** Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 600V 7A TO-220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# STP9NK60Z Specifications

Manufacturer Part Number         STP9NK60Z           Manufacturer         STMicroelectronics           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         SuperMESH?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         7A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4.5V @ 100µA           Gate Charge (Qg) (Max) @ Vgs         53nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1110pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         125W (Tc)           Rds On (Max) @ Id, Vgs         950 mOhm @ 3.5A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220-3           Report errors?		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         SuperMESH?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         7A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4.5V @ 100μA           Gate Charge (Qg) (Max) @ Vgs         53nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1110pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         125W (Tc)           Rds On (Max) @ Id, Vgs         950 mOhm @ 3.5A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220AB	Manufacturer Part Number	STP9NK60Z
Package         TO-220-3           Series         SuperMESH?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         7A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4.5V @ 100μA           Gate Charge (Qg) (Max) @ Vgs         53nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1110pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         125W (Tc)           Rds On (Max) @ Id, Vgs         950 mOhm @ 3.5A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220-3	Manufacturer	STMicroelectronics
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Series         SuperMESH?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         600V           Current - Continuous Drain (Id) @ 25°C         7A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4.5V @ 100μA           Gate Charge (Qg) (Max) @ Vgs         53nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1110pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         125W (Tc)           Rds On (Max) @ Id, Vgs         950 mOhm @ 3.5A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB           Package / Case         TO-220-3		Transistors - FETs, MOSFETs - Single
FET Type N-Channel  Technology MOSFET (Metal Oxide)  Four to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C TA (Tc)  Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs SanC @ 10V  Input Capacitance (Ciss) (Max) @ Vds Vgs (Max)  FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 950 mOhm @ 3.5A, 10V  Operating Temperature Mounting Type Supplier Device Package Package / Case  N-Channel N-Channel NOSFET (Metal Oxide)  800V  74 (Tc)  74 (Tc)  75 (To)  74 (Tc)  75 (To)  75 (TJ)	Package	TO-220-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 7A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Supplier Device Package Package / Case  MOSFET (Metal Oxide) 600V  7A (Tc)	Series	SuperMESH?
Drain to Source Voltage (Vdss)600 VCurrent - Continuous Drain (Id) @ 25°C7A (Tc)Drive Voltage (Max Rds On, Min Rds On)10 VVgs(th) (Max) @ Id4.5 V @ 100 μAGate Charge (Qg) (Max) @ Vgs53nC @ 10 VInput Capacitance (Ciss) (Max) @ Vds1110pF @ 25 VVgs (Max)±30 VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs950 mOhm @ 3.5A, 10 VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  For Vgs (Max)  FET Peature  Power Dissipation (Max)  Toperating Temperature  Toperating Temperature  Toperating Type  Through Hole  Supplier Device Package  Package / Case  Toperating To	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 100μAGate Charge (Qg) (Max) @ Vgs53nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1110pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs950 mOhm @ 3.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id       4.5V @ 100μA         Gate Charge (Qg) (Max) @ Vgs       53nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1110pF @ 25V         Vgs (Max)       ±30V         FET Feature       -         Power Dissipation (Max)       125W (Tc)         Rds On (Max) @ Id, Vgs       950 mOhm @ 3.5A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)         Mounting Type       Through Hole         Supplier Device Package       TO-220AB         Package / Case       TO-220-3	Current - Continuous Drain (Id) @ 25°C	7A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  1110pF @ 25V  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  125W (Tc)  Mounting Type  Through Hole  Supplier Device Package  TO-220AB  Package / Case  53nC @ 10V  1110pF @ 25V  11	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  Package / Case  TO-220-3	Vgs(th) (Max) @ Id	4.5V @ 100μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs950 mOhm @ 3.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	53nC @ 10V
FET Feature - Power Dissipation (Max) 125W (Tc) Rds On (Max) @ Id, Vgs 950 mOhm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	1110pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  950 mOhm @ 3.5A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220AB  Package / Case  TO-220-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs950 mOhm @ 3.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220AB  Package / Case TO-220-3	Power Dissipation (Max)	125W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	950 mOhm @ 3.5A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

#### STP9NK60Z Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## STP9NK60Z Payment Methods



















## STP9NK60Z Shipping Methods













If you have any question about STP9NK60Z, please do not hesitate to contact us!

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